

ABSTRACT OF THE DISCLOSURE

A novel heat treatment apparatus is provided which comprises a first tube, a second tube placed therein, and a heater, and heat-treats a semiconductor article in the second tube in an atmospheric gas, wherein at least an internal face of the second tube is constructed from non-silicon oxide, and the first tube is constructed from vitreous silica. Thereby, hydrogen gas is fed to a wafer without passing over a face comprised of silicon oxide heated to a high temperature. This apparatus prevents metal contamination of the wafer by fused quartz tube as the contamination source, and also prevents etching of silicon by reaction of silicon oxide and silicon.

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